HALOGEN

FREE





P-Channel 1.8 V (G-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
- 12	0.165 at V _{GS} = - 4.5 V	- 0.95		
	0.220 at V _{GS} = - 2.5 V	- 0.82		
	0.280 at V _{GS} = - 1.8 V	- 0.67		

SC-89 (6-LEADS) D 1 6 D Marking Code G 3 View Marking Code O WL Lot Traceability and Date Code Part Number Code

Ordering Information: Si1039X-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Low Threshold
- Smallest LITTLE FOOT[®] Package:
 1.6 mm x 1.6 mm
- Low 0.6 mm Profile
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- Cell Phones and Pagers
 - Load Switch

ABSOLUTE MAXIMUM RATINGS ((T _A = 25 °C, unle	ess otherwise	noted)		
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 12		V
Gate-Source Voltage		V _{GS}	± 8		
Continuous Drain Current /T 150 °C\8	T _A = 25 °C	- I _D	- 0.95	- 0.87	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 0.76	- 0.69	
Pulsed Drain Current		I _{DM}	- 4		Α
Continuous Diode Current (Diode Conduction) ^a		I _S	- 0.18	- 0.14	
Maximum Davier Dissipations	T _A = 25 °C	- P _D	0.21	0.17	W
Maximum Power Dissipation ^a	T _A = 70 °C		0.13	0.10	
Operating Junction and Storage Temperature Range		T _J , T _{stq}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 5 s	- R _{thJA}	500	600	°C/W
	Steady State		600	720	C/VV

Notes:

a. Surface mounted on 1" x 1" FR4 board with minimum copper.

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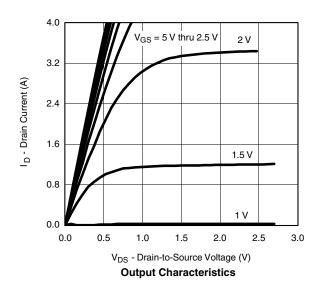
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	- 0.45			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 12 V, V _{GS} = 0 V			- 1	uА	
		V _{DS} = - 12 V, V _{GS} = 0 V, T _J = 70 °C			- 5		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 4.5 V	- 4			Α	
		V _{GS} = - 4.5 V, I _D = - 0.87 A		0.140	0.165		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 0.75 A		0.180	0.220	Ω	
		V _{GS} = - 1.8 V, I _D = - 0.2 A		0.230	0.280		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 0.87 A		3.5		S	
Diode Forward Voltage ^a	V_{SD}	I _S = - 0.14 A, V _{GS} = 0 V		- 0.78	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Q_g			3.8	6		
Gate-Source Charge	Q _{gs}	$V_{DS} = -6 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -0.87 \text{ A}$		0.7		nC	
Gate-Drain Charge	Q_{gd}			0.8			
Turn-On Delay Time	t _{d(on)}			15	30		
Rise Time	t _r	V_{DD} = - 6 V, R_L = 12 Ω		20	40	ns	
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong\text{-}\ 0.5\ \text{A},\ \text{V}_\text{GEN}=\text{-}\ 4.5\ \text{V},\ \text{R}_g=6\ \Omega$		30	60		
Fall Time	t _f			16	30		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 0.14 A, dI/dt = 100 A/μs		20	40		

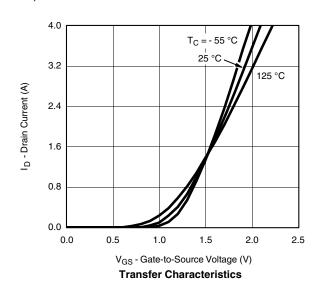
Notes:

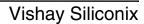
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





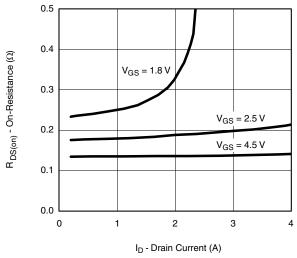




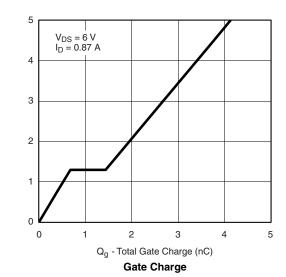
V_{GS} - Gate-to-Source Voltage (V)

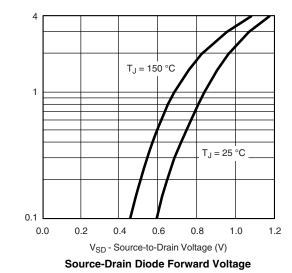
Is - Source Current (A)

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



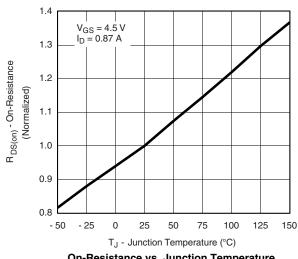
On-Resistance vs. Drain Current



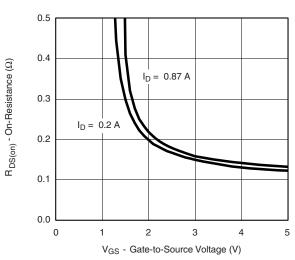


800 600 C - Capacitance (pF) 400 Coss 200 0 2 10 12 0 6

V_{DS} - Drain-to-Source Voltage (V) Capacitance



On-Resistance vs. Junction Temperature

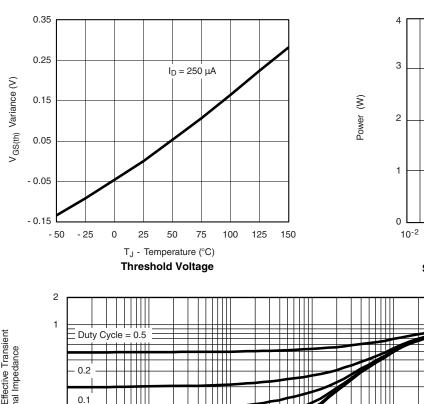


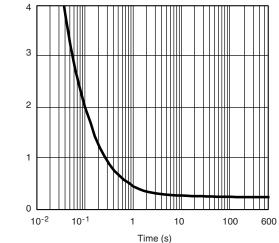
On-Resistance vs. Gate-to-Source Voltage

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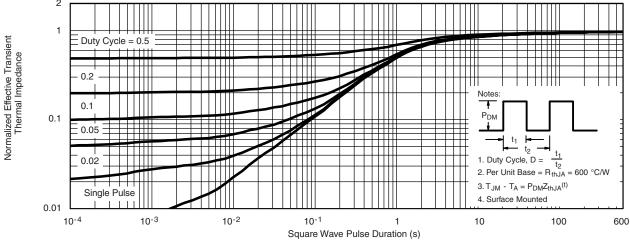
VISHAY.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient

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